L Number	Hits	Search Text	DB	Time stamp
1	16	<pre>@ad<=20011206 and 'silicon oxynitride' same 'silane' same 'dichlorosilane'</pre>	USPAT; US-PGPUB; EPO; JPO; DERWENT;	2003/06/20 09:09
2	2	<pre>@ad<=20011206 and 'SiON' same 'silane' same 'dichlorosilane'</pre>	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2003/06/20 09:07
-	696	(438/400).ccls. and @ad<=20011206	IBM_TDB USPAT; US-PGPUB; EPO; JPO;	2002/05/17
_	6	((438/400).ccls. and @ad<=20011206) and ONO	DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/05/17
-	0	@ad<=20011206 and 'ONO structure' with 'buffer layer'	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/05/17 12:35
_	290	@ad<=20011206 and 'ONO structure'	IBM_TDB USPAT; US-PGPUB; EPO; JPO;	2002/05/17 12:01
_	160	@ad<=20011206 and 'Oxide' with 'SiON' with 'SiN' with 'SiON' with 'Oxide'	DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/05/17
-	3	<pre>@ad<=20011206 and 'ONO structure' and 'buffer layer'</pre>	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/05/17 12:40
_	1	@ad<=20011206 and 'multi dielectric layer' and 'memory'	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/05/17 12:43
-	26	@ad<=20011206 and 'multi' adj 'dielectric' and 'memory'	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/05/17 12:47
-	0	@ad<=20011206 and 'O-SiON-N-SiON-O'	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/05/17 12:49
_	1393	@ad<=20011206 and oxide and SiON and Nitride and SiON and oxide	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/05/17 12:55
-	o	@ad<=20011206 and oxide adj SiON adj Nitride adj SiON adj oxide	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/17 12:56

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_	300	@ad<=20011206 and 'oxide' with 'SiON'	USPAT;	2002/05/17
		with 'nitride' with 'SiON' with 'oxide'	US-PGPUB;	14:31
			EPO; JPO;	
			DERWENT;	
	107	(0-4, 2001120C and landdal adth (CiON)	IBM_TDB	2003/06/10
-	107	(@ad<=20011206 and 'oxide' with 'SiON' with 'nitride' with 'SiON' with	USPAT; US-PGPUB;	2003/06/19 14:52
			EPO; JPO;	14:52
		'oxide') and memory	DERWENT;	
			IBM TDB	
_	540	@ad<=20011206 and (438/778).ccls.	USPAT;	2002/05/17
	340	Gad	US-PGPUB;	14:32
			EPO; JPO;	11102
			DERWENT;	
			IBM TDB	
-	2862	((438/778) or (438/787) or	USPĀT;	2002/10/28
		(438/790-791) or (438/794) or (438/400)	US-PGPUB;	08:49
		or (438/769-770) or (438/770) or	EPO; JPO;	
		(438/775)).CCLS.	DERWENT;	
			IBM_TDB	
-	2356	((257/324) or (257/314-315) or	USPAT;	2002/10/28
		(257/406) or (257/410)).CCLS.	US-PGPUB;	08:41
			EPO; JPO;	
			DERWENT;	
		(((420 /770) (420 /707)	IBM_TDB	2002/10/29
-	7	((,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,	USPAT;	2002/10/28
		(438/790-791) or (438/794) or (438/400)	US-PGPUB; EPO; JPO;	08:59
		or (438/769-770) or (438/770) or (438/775)).CCLS.) and @ad<=20011206 and	DERWENT;	
		'silane' with 'nitrogen oxide'	IBM TDB	
_	6328	(((438/778) or (438/787) or	USPAT;	2002/10/28
	0520	(438/790-791) or (438/794) or (438/400)	US-PGPUB;	09:03
1		or (438/769-770) or (438/770) or	EPO; JPO;	
		(438/775)).CCLS.) and @ad<=20011206 and	DERWENT;	
		'SiON' or 'silicon oxynitride'	IBM TDB	
_	0	(((438/778) or (438/787) or	USPĀT;	2002/10/28
		(438/790-791) or (438/794) or (438/400)	US-PGPUB;	09:04
		or (438/769-770) or (438/770) or	EPO; JPO;	
		(438/775)).CCLS.) and @ad<=20011206 and	DERWENT;	
		SiH4 with N2O with NH3	IBM_TDB	0000/10/00
-	8		USPAT;	2002/10/28
		(438/790-791) or (438/794) or (438/400)	US-PGPUB;	09:09
		or (438/769-770) or (438/770) or	EPO; JPO; DERWENT;	
		(438/775)).CCLS.) and @ad<=20011206 and 'SiON' with 'deposition'	IBM TDB	
1_	119	(((438/778) or (438/787) or	USPAT;	2002/10/28
_	130	((438/790-791) or (438/794) or (438/400)	US-PGPUB;	09:11
		or (438/769-770) or (438/770) or	EPO; JPO;	
		(438/775)).CCLS.) and @ad<=20011206 and	DERWENT;	
		'ammonia'	IBM_TDB	
-	190	(((438/778) or (438/787) or	USPAT;	2002/10/28
		(438/790-791) or (438/794) or (438/400)	US-PGPUB;	09:11
		or (438/769-770) or (438/770) or	EPO; JPO;	
		(438/775)).CCLS.) and @ad<=20011206 and	DERWENT;	
		'ammonia' and 'silane'	IBM_TDB	2002/10/22
-	194	, =	USPAT;	2002/10/28
		'silane' and 'nitrogen oxide'	US-PGPUB;	09:16
			EPO; JPO; DERWENT;	
			IBM TDB	
_	359	@ad<=20011206 and 'oxide' with 'SiON'	USPAT;	2003/02/13
-	339	with 'nitride' with 'SiON' with 'oxide'	US-PGPUB;	13:27
		with interface with Sion with Oxide	EPO; JPO;	
			DERWENT;	
			IBM TDB	
-	27	@ad<=20011206 and 'ammonia' same	USPAT;	2002/10/28
		'silane' same 'nitrogen oxide'	US-PGPUB;	09:19
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	

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		0 1 00011006		10000 /00 /00
_		<pre>@ad<=20011206 and 'oxide' same 'silane'</pre>	USPAT;	2003/02/13
		same dichloro adj silane with 'nitrogen	US-PGPUB;	13:29
		oxide'	EPO; JPO;	
İ			DERWENT;	
			IBM_TDB	
-	0	@ad<=20011206 and 'silane' same	USPAT;	2003/02/13
		'dichloro silane' with 'nitrogen oxide'	US-PGPUB;	13:30
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
-	3	@ad<=20011206 and 'silane' same	USPAT;	2003/02/13
		'dichlorosilane' with 'N.sub.20'	US-PGPUB;	13:36
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
-	0	@ad<=20011206 and 'silicon oxide' same	USPAT;	2003/02/13
		'silane' same 'DCS' same 'N.sub.20'	US-PGPUB;	13:37
			EPO; JPO;	13.37
Ì			DERWENT;	
	1		IBM TDB	
_	32	@ad<=20011206 and 'silicon oxide' same	USPAT;	2003/02/13
	1	'silane' same 'N.sub.20'	US-PGPUB;	13:39
		SITAME SAME N.SUD.20	-	13:39
			EPO; JPO;	
			DERWENT;	
		0-420011206	IBM_TDB	2002/25/25
-	25	• · · · · · · · · · · · · · · · · · ·	USPAT;	2003/06/19
		'silane' same 'nitrous oxide' and	US-PGPUB;	10:17
		'dichlorosilane'	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
_	71	@ad<=20011206 and 'oxide' same 'silane'	USPAT;	2003/06/19
		same 'nitrous oxide' same	US-PGPUB;	10:51
	1	'dichlorosilane'	EPO; JPO;	
			DERWENT;	1
			IBM TDB	1
_	12	@ad<=20011206 and 'oxide' same	USPAT;	2003/06/19
		'SiH.sub.4' same 'N.sub.20' same	US-PGPUB;	10:29
		'SiH.sub.2Cl.sub.2'	EPO; JPO;	
			DERWENT;	
			IBM TDB	
_	4	@ad<=20011206 and 'silicon oxide' same	USPĀT;	2003/06/19
	1	'SiH.sub.4' same 'N.sub.20' same	US-PGPUB;	10:37
		'SiH.sub.2Cl.sub.2'	EPO; JPO;	
1			DERWENT;	
			IBM TDB	(
_	5	(("6127255") or ("5811316") or	USPAT;	2003/06/19
		("5331191") or ("5202275")).PN.	US-PGPUB;	10:37
		\ 3331131 O1 \ 3202213 .FN.	EPO; JPO;	10.57
			DERWENT;	
_	27	02d<-20011206 and 1diamidal area	IBM_TDB	2002/06/20
1 -	27	• • • • • • • • • • • • • • • • • • • •	USPAT;	2003/06/20
		'silane' same 'nitrous oxide' same	US-PGPUB;	09:06
		'dichlorosilane'	EPO; JPO;	Į
			DERWENT;	
		(0.1,00041006	IBM_TDB	0000 105 155
-	160	(@ad<=20011206 and 'oxide' with 'SiON'	USPAT;	2003/06/19
		with 'nitride' with 'SiON' with	US-PGPUB;	15:20
		'oxide') and memory	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	1	"5506178".PN.	USPĀT	2003/06/19
				15:06
-	45	hisatomi-kiyoshi.in.	USPAT;	2003/06/19
		_	US-PGPUB;	15:25
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
	ı			·

_	20	toshiba.as. an	d 'ONO' and 'oxynitride'	USPAT;	2003/06/19
				US-PGPUB;	15:28
				EPO; JPO;	j i
				DERWENT;	
				IBM_TDB]
-	341	toshiba.as. an	d 'oxynitride'	USPAT;	2003/06/19
				US-PGPUB;	15:29
				EPO; JPO;]
				DERWENT;)
				IBM TDB)